

TOSHIBA Transistor Silicon NPN / PNP Epitaxial Type (PCT Process)

TPCP8901

Portable Equipment Applications
Switching Applications

Unit: mm

- Small footprint due to small and thin package
- High DC current gain : PNP $h_{FE} = 200$ to 500 ($I_C = -0.1$ A)
: NPN $h_{FE} = 400$ to 1000 ($I_C = 0.1$ A)
- Low collector-emitter saturation : PNP $V_{CE(sat)} = -0.20$ V (max)
: NPN $V_{CE(sat)} = 0.17$ V (max)
- High-speed switching : PNP $t_f = 70$ ns (typ.)
: NPN $t_f = 85$ ns (typ.)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

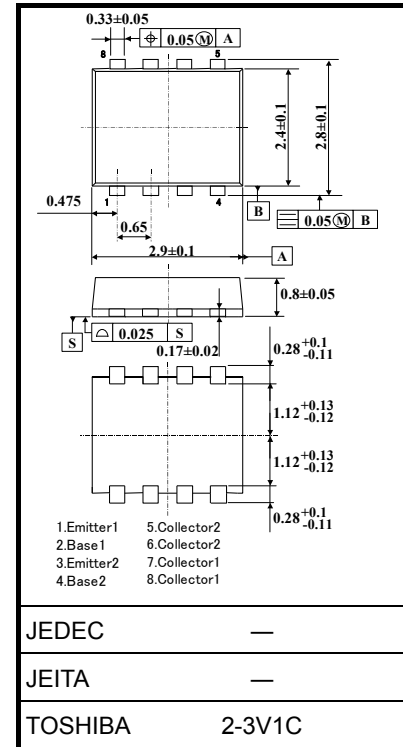
Characteristics		Symbol	Rating		Unit
			PNP	NPN	
Collector-base voltage		V_{CBO}	-50	100	V
Collector-emitter voltage		V_{CEO}	-50	50	V
Emitter-base voltage		V_{EBO}	-7	7	V
Collector current	DC (Note 1)	I_C	-0.8	1.0	A
	Pulse (Note 1)	I_{CP}	-5.0	5.0	
Base current		I_B	-100	100	mA
Collector power dissipation ($t = 10\text{s}$)	Single-device operation	P_C (Note 2)	1.48		W
	Single-device value at dual operation		0.80		
Collector power dissipation (DC)	Single-device operation	P_C (Note 2)	0.83		W
	Single-device value at dual operation		0.48		
Junction temperature		T_j	150		$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150		$^\circ\text{C}$

Note 1: Please use devices on condition that the junction temperature is below 150°C .
 $I_{cp} = \pm 5\text{A}$ (@ $t \leq 100 \mu\text{s}$)

Note 2: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm^2)

Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.017 g (typ.)

Figure 1. Circuit configuration (top view)

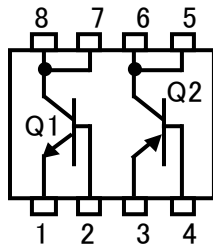
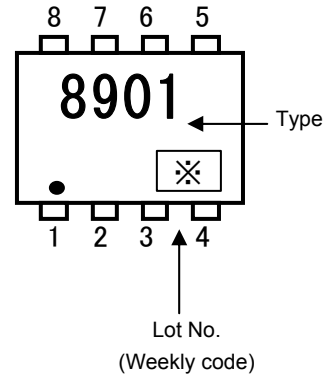
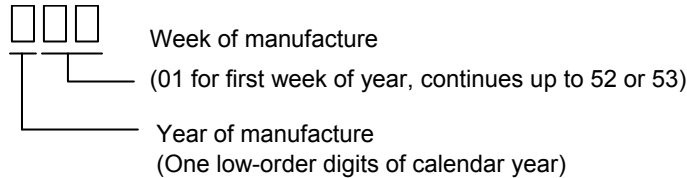


Figure 2. Marking (Note 4)



Note 4: ● on lower left on the marking indicates Pin 1.

※ Weekly code: (Three digits)



Electrical Characteristics (Ta = 25°C)

PNP

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -7\text{ V}, I_C = 0$	—	—	-100	nA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-50	—	—	V
DC current gain	$h_{FE(1)}$	$V_{CE} = -2\text{ V}, I_C = -0.1\text{ A}$	200	—	500	
	$h_{FE(2)}$	$V_{CE} = -2\text{ V}, I_C = -0.3\text{ A}$	125	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -0.3\text{ A}, I_B = -0.01\text{ A}$	—	—	-0.20	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -0.3\text{ A}, I_B = -0.01\text{ A}$	—	—	-1.10	V
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	8	—	pF
Switching time	Rise time	See Figure 3 circuit diagram $V_{CC} \approx -30\text{ V}, R_L = 100\ \Omega$ $-I_{B1} = I_{B2} = -10\text{ mA}$	—	60	—	ns
	Storage time		—	280	—	
	Fall time		—	70	—	

NPN

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 100\text{ V}, I_E = 0$	—	—	100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 7\text{ V}, I_C = 0$	—	—	100	nA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	50	—	—	V
DC current gain	$h_{FE(1)}$	$V_{CE} = 2\text{ V}, I_C = 0.1\text{ A}$	400	—	1000	
	$h_{FE(2)}$	$V_{CE} = 2\text{ V}, I_C = 0.3\text{ A}$	200	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 300\text{ mA}, I_B = 6\text{ mA}$	—	—	0.17	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 300\text{ mA}, I_B = 6\text{ mA}$	—	—	1.10	V
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	5	—	pF
Switching time	Rise time	See Figure 4 circuit diagram $V_{CC} \approx 30\text{ V}, R_L = 100\ \Omega$ $I_{B1} = -I_{B2} = 10\text{ mA}$	—	35	—	ns
	Storage time		—	680	—	
	Fall time		—	85	—	

Figure 3. Switching Time Test Circuit & Timing Chart

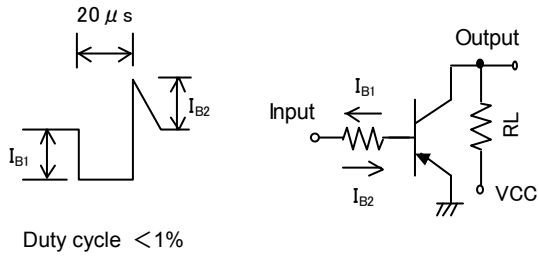
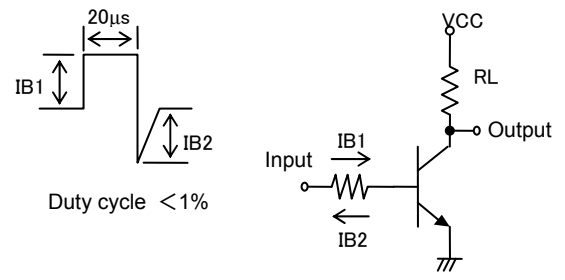
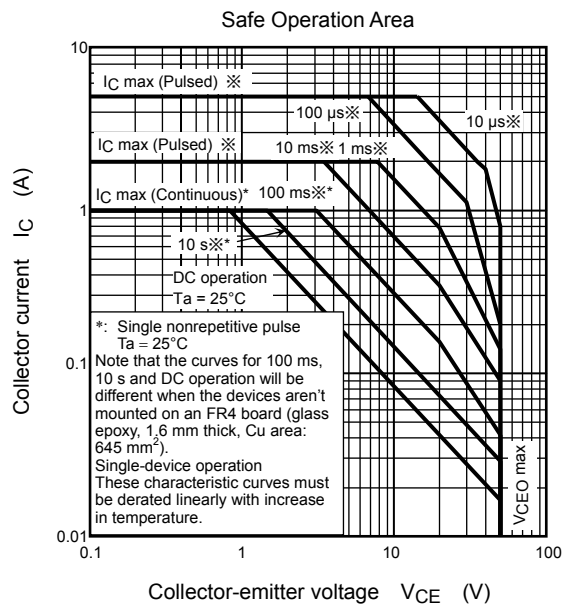
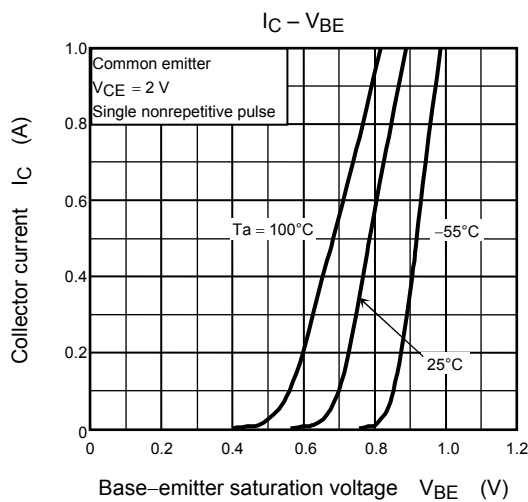
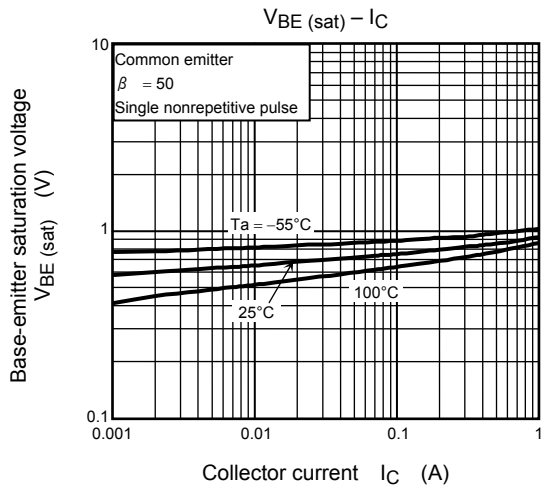
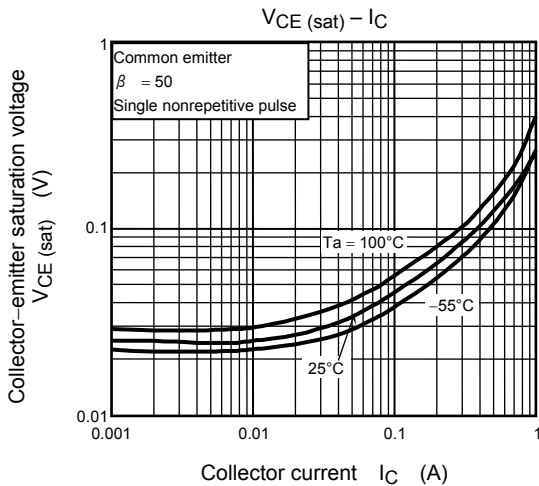
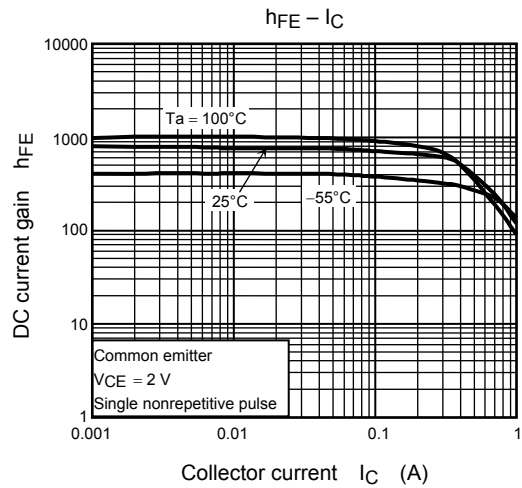
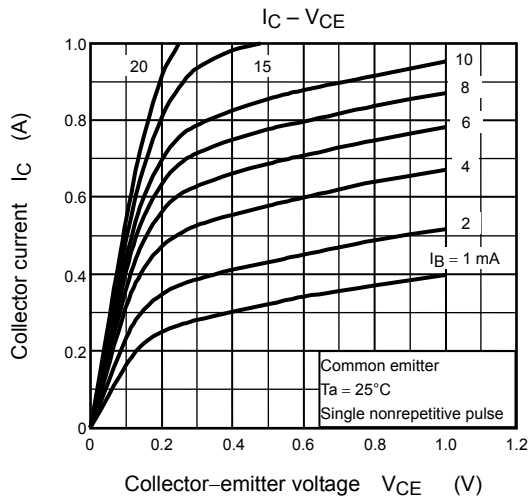


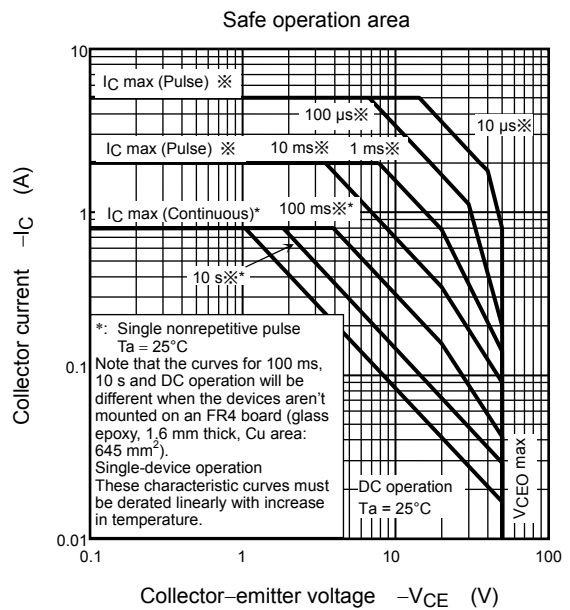
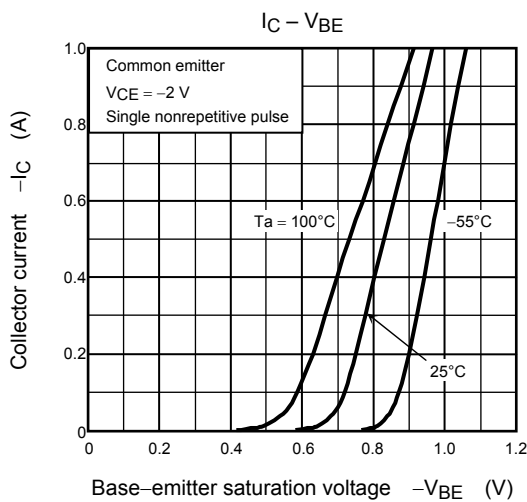
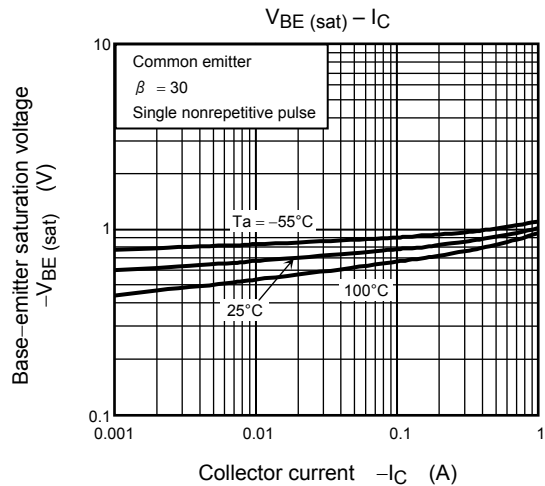
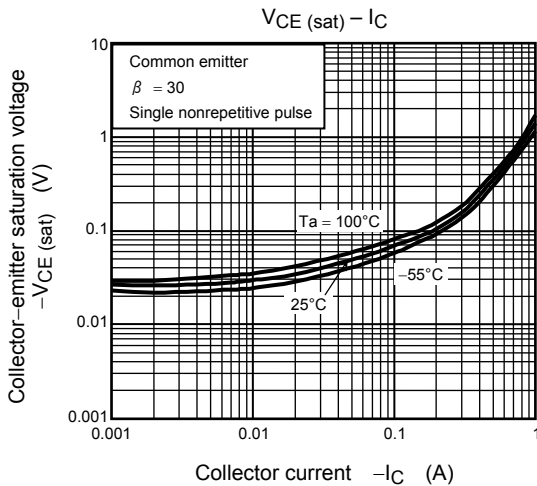
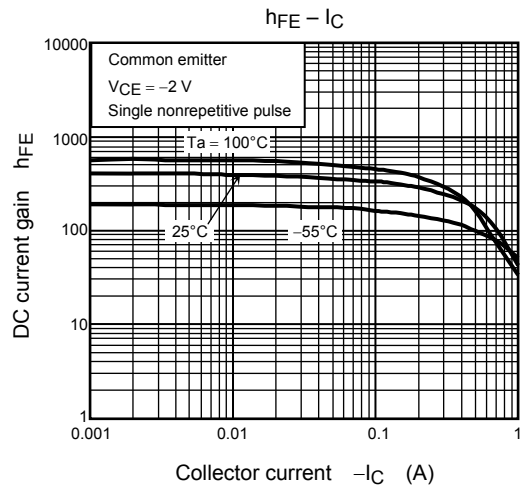
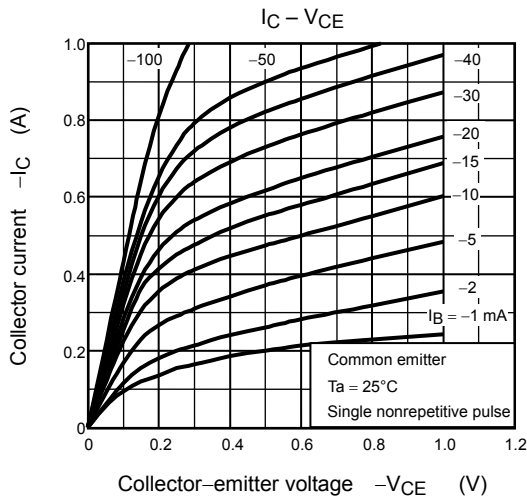
Figure 4. Switching Time Test Circuit & Timing Chart



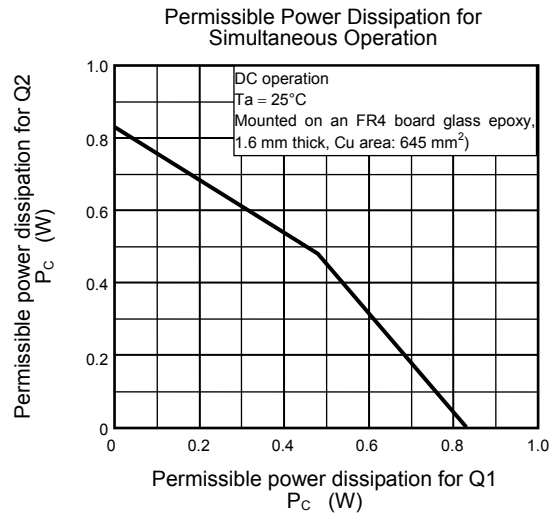
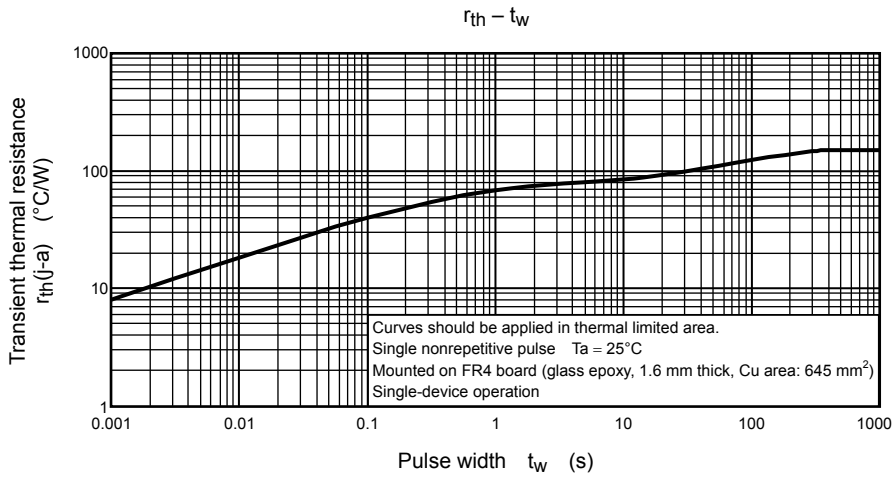
NPN



PNP



Common



Collector power dissipation at the single-device operation is 0.83W.
 Collector power dissipation at the single-device value at dual operation is 0.48W.
 Collector power dissipation at the dual operation is set to 0.96W.

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